## **Triacs**

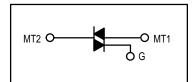
# **Silicon Bidirectional Thyristors**

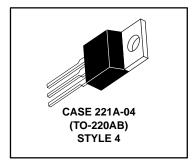
... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- TO-220 Construction Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC218 Series) or Four Modes (MAC218A Series)

# MAC218 Series MAC218A Series

TRIACs 8 AMPERES RMS 200 thru 800 VOLTS





#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted.)

Rat	ing	Symbol	Value	Unit
Peak Repetitive Off-State Voltage(1) (Gate Open, T <sub>J</sub> = 25 to 125°C)	MAC218-4, MAC218A4 MAC218-6, MAC218A6 MAC218-8, MAC218A8 MAC218-10, MAC218A10	VDRM	200 400 600 800	Volts
On-State Current RMS (Conduction Angle = 360°, T <sub>C</sub> = +80°C	C)	I <sub>T(RMS)</sub>	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = 80°C, pre	eceded and followed by rated current)	ITSM	100	Amps
Fusing Current (t = 8.3 ms)		l <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 2 μs)		PGM	16	Watts
Average Gate Power (T <sub>C</sub> = +80°C, t = 8.3 ms)		P <sub>G(AV)</sub>	0.35	Watt
Peak Gate Trigger Current (Pulse Width = 1 µs)		I <sub>GTМ</sub>	4	Amps
Operating Junction Temperature Range	-	TJ	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

<sup>1.</sup> V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



#### **MAC218 Series MAC218A Series**

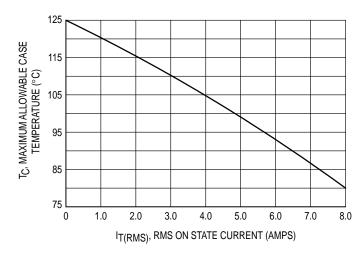
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.2	°C/W

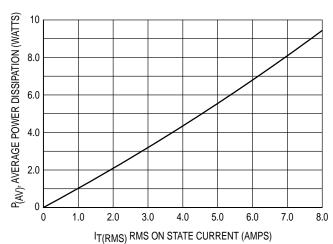
### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current $(V_D = Rated \ V_{DRM}, \ gate \ open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	IDRM	_	_	10 2	μA mA
Peak On-State Voltage (Either Direction) (ITM = 11.3 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle < 2%)	V <sub>TM</sub>	_	1.7	2	Volts
Gate Trigger Current (Continuous dc) $ (V_D = 12 \text{ Vdc}, R_L = 12\Omega) $	l <sub>GT</sub>	=	_ _	50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L$ = 100 Ohms) MT2(+), $G(+)$ MT2(+), $G(-)$ MT2(-), $G(-)$ MT2(-), $G(-)$ MT2(-), $G(+)$ "A" SUFFIX ONLY (Main Terminal Voltage = Rated VDRM, $R_L$ = 10 k $\Omega$ , $T_J$ = +125°C) MT2(+), $G(+)$ ; MT2(-), $G(-)$ ; MT2(+), $G(-)$ MT2(-), $G(+)$ "A" SUFFIX ONLY	VGT		0.9 0.9 1.1 1.4	2 2 2 2.5 —	Volts
Holding Current (Either Direction) (VD = 24 Vdc, Gate Open, Initiating Current = 200 mA)	lн	_	_	50	mA
Critical Rate of Rise of Commutating Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C$ = 80°C)	dv/dt(c)		5	_	V/μs
Critical Rate of Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open, $T_J$ = 125°C)	dv/dt	_	100	_	V/µs

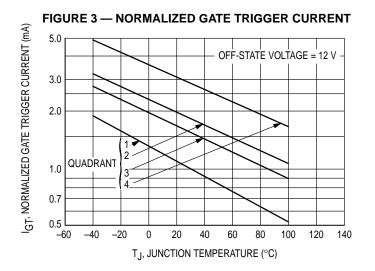
#### FIGURE 1 — CURRENT DERATING

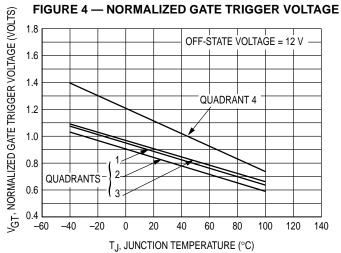


#### FIGURE 2 — POWER DISSIPATION

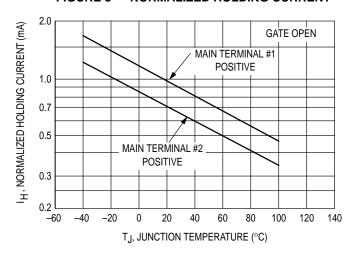


#### **MAC218 Series MAC218A Series**

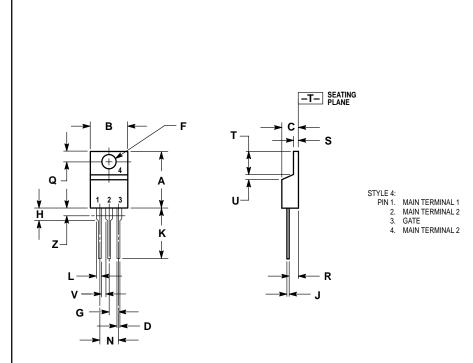




#### FIGURE 5 — NORMALIZED HOLDING CURRENT



#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   A
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
٦	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Ø	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

CASE 221A-04 (TO-220AB)

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MAC218/D